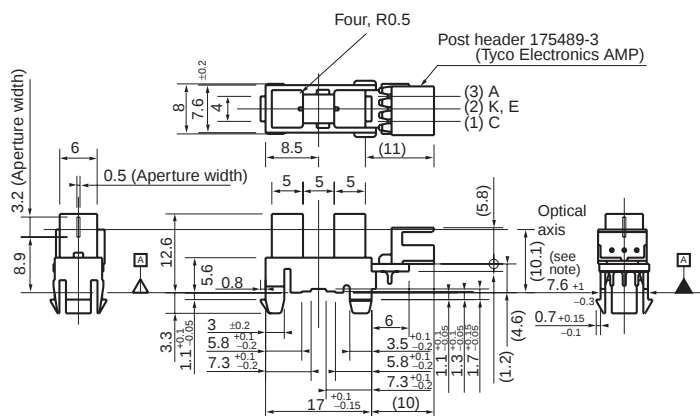


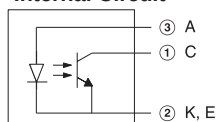
Photomicrosensor (Transmissive) EE-SX1235A-P2

■ Dimensions

Note: All units are in millimeters unless otherwise indicated.



Internal Circuit



Note: The asterisked dimension is specified by datum A only.

Unless otherwise specified, the tolerances are as shown below.

Dimensions	Tolerance
3 mm max.	±0.3
3 < mm ≤ 6	±0.375
6 < mm ≤ 10	±0.45
10 < mm ≤ 18	±0.55
18 < mm ≤ 30	±0.65

Terminal No.	Name
A	Anode
C	Collector
K, E	Cathode, Emitter

Recommended Mating Connectors:

Tyco Electronics AMP 173977-3 (press-fit connector)
175778-3 (crimp connector)
179228-3 (crimp connector)

■ Features

- Snap-in mounting model.
- Mounts to 1.0-, 1.2- and 1.6-mm-thick PCBs.
- High resolution with a 0.5-mm-wide aperture.
- 5-mm-wide slot.
- Connects to Tyco Electronics AMP's CT-series connectors.

■ Absolute Maximum Ratings (Ta = 25°C)

Item		Symbol	Rated value
Emitter	Forward current	I_F	50 mA (see note)
	Pulse forward current	I_{FP}	---
	Reverse voltage	V_R	4 V
Detector	Collector–Emitter voltage	V_{CEO}	30 V
	Emitter–Collector voltage	V_{ECO}	5 V
	Collector current	I_C	20 mA
	Collector dissipation	P_C	100 mW (see note)
Ambient temperature	Operating	T_{opr}	–25°C to 95°C
	Storage	T_{stg}	–40°C to 100°C
Soldering temperature		T_{sol}	---

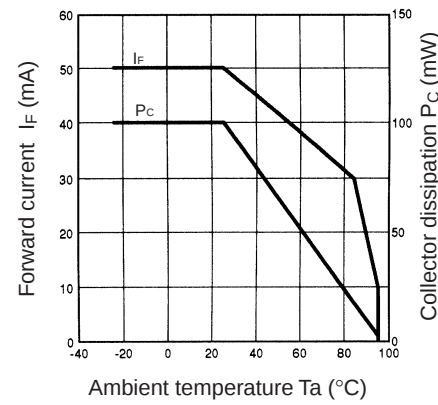
Note: Refer to the temperature rating chart if the ambient temperature exceeds 25°C.

■ Electrical and Optical Characteristics (Ta = 25°C)

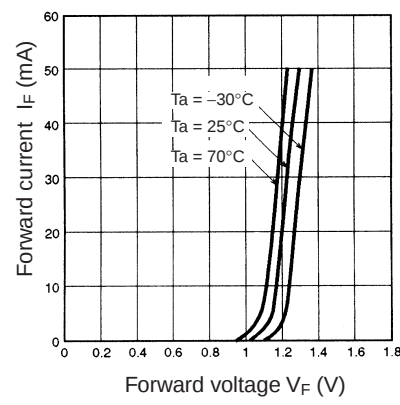
Item		Symbol	Value	Condition
Emitter	Forward voltage	V_F	1.2 V typ., 1.5 V max.	$I_F = 30 \text{ mA}$
	Reverse current	I_R	0.01 μA typ., 10 μA max.	$V_R = 4 \text{ V}$
	Peak emission wavelength	λ_P	940 nm typ.	$I_F = 30 \text{ mA}$
Detector	Light current	I_L	0.6 mA min., 14 mA max.	$I_F = 20 \text{ mA}$, $V_{CE} = 5 \text{ V}$
	Dark current	I_D	200 nA max.	$V_{CE} = 10 \text{ V}$, 0 ℓx
	Leakage current	I_{LEAK}	---	---
	Collector–Emitter saturated voltage	$V_{CE}(\text{sat})$	0.1 V typ., 0.4 V max.	$I_F = 20 \text{ mA}$, $I_L = 0.3 \text{ mA}$
	Peak spectral sensitivity wavelength	λ_P	850 nm typ.	$V_{CE} = 5 \text{ V}$
Rising time		t_r	8 μs typ.	$V_{CC} = 5 \text{ V}$, $R_L = 100 \Omega$, $I_L = 1 \text{ mA}$
Falling time		t_f	8 μs typ.	$V_{CC} = 5 \text{ V}$, $R_L = 100 \Omega$, $I_L = 1 \text{ mA}$

Engineering Data

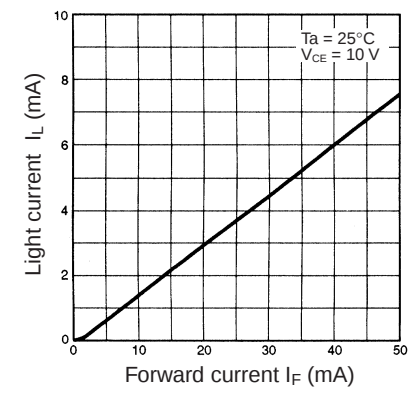
Forward Current vs. Collector Dissipation Temperature Rating



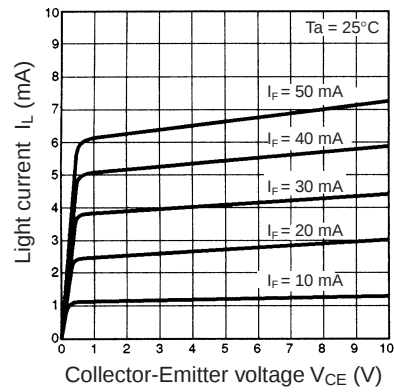
Forward Current vs. Forward Voltage Characteristics (Typical)



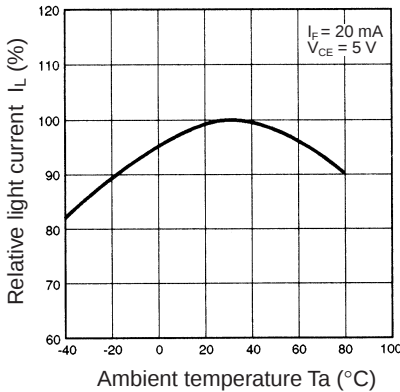
Light Current vs. Forward Current Characteristics (Typical)



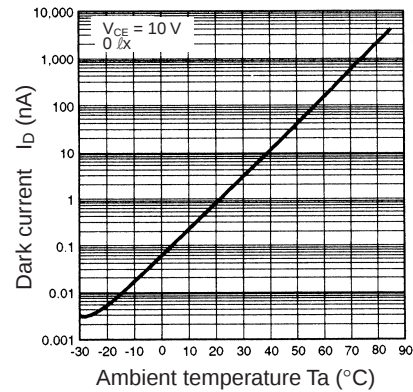
Light Current vs. Collector-Emitter Voltage Characteristics (Typical)



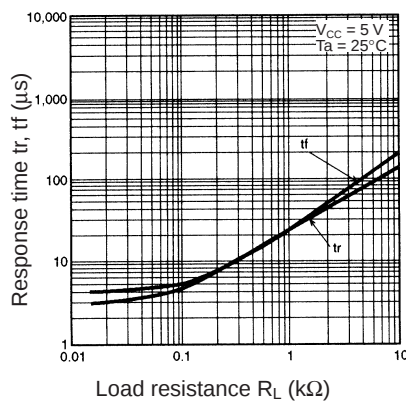
Relative Light Current vs. Ambient Temperature Characteristics (Typical)



Dark Current vs. Ambient Temperature Characteristics (Typical)

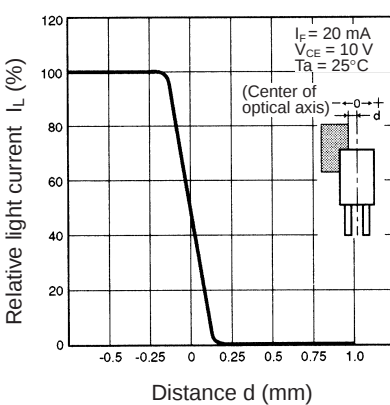


Response Time vs. Load Resistance Characteristics (Typical)



Refer to EE-SX4235A-P2 on page 200.

Sensing Position Characteristics (Typical)



Response Time Measurement Circuit

